

Citations for Ion : **Bi**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Num
1966	Nielsen, O 'Specialeopgave' <i>Niels Bohr Institute, University of Copenhagen, Pp. 1-64 (1966)</i> <i>Comment : S, dS. 50 keV C, Na, Cl, K, Mn, Y, Zn, Ag, Hf, Lu, Hg, Bi -> H2, D2, He, N2, Ne, Ar</i>	1966-Niel
1970	Eldridge, G. Govind, P. K. Nieman, D. A. Chernow, F. 'Radiation Damage Studies of Bismuth Ion-Implanted CdS' <i>Proc. of the European Conference on Ion Implantation. Peter Peregrinus, Publisher, Stevenhage, England, P. 143-48 (1970)</i> <i>Comment : R, dR. 25 keV Bi -> CdS</i>	1970-Eldr
1971	Sigurd, D. Domeij, B. 'Critical Angles of Sb and Bi Implanted Si' <i>Phys. Letters, 36A, 81-82 (1971)</i> <i>Comment : R. 40 keV Sb, Bi -> Si ([111], [110], [100])</i>	1971-Sigu
1973	Eldridge, G. Chernow, F. Rise, G. 'Further Studies of Bismuth-Implanted Cadmium Sulfide' <i>J. Appl. Phys., 44, 3858-61 (1973)</i> <i>Comment : R,dR. 25 keV 209Bi -> CdS (Cryst.)</i>	1973-Eldr
1974	Grant, W. A. Williams, J. S. Dodds, D. 'Measurement of Projected and Lateral Range Parameters for Low Energy Heavy Ions in Silicon by Rutherford Backscattering' <i>Meyer, G. Linker and F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 235-44 (1974)</i> <i>Comment : R, dR, dR(Lateral). 10-80 keV Pb, 50-400 keV Bi, 40 keV Ar, Cu, Kr, Cd, Al, Dy, W -> Si</i>	1974-Gran
1975	Williams, J. S. Grant, W. A. 'High Resolution Rutherford Backscattering and Its Application to Ion Range and Ion Collectionrad' <i>Rad. Effects, 25, 55-56 (1975)</i> <i>Comment : R, dR. 20-80 keV Kr, Xe, Cs, Dy, Au, Pb, Bi -> Si, Al</i>	1975-Will
1976	Callaghan, P. T. Kittel, P. Stone, N. J. Johnson, P. D. 'Impurity-Site Distribution of Implanted Bi in Iron and Nickel Studied by Channeling and Nuclear Orientation' <i>Phys. Rev. B, 14, 3722-31 (1976)</i> <i>Comment : R, dR, 200 keV Bi -> Fe, Ni (Cryst. Chann. And Random)</i>	1976-Call
1976	Grant, W. A. Williams, J. S. Dodds, D. 'Measurement of the Lateral Spread of Heavy Ions Implanted into Silicon' <i>Rad. Effects, 29, 189-90 (1976)</i> <i>Comment : dR(Lateral). (10-40 keV) Cu, Cd, Xe, Dy, Kr, W, Pb, Bi -> Si</i>	1976-Gran3

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1976	Hirvonen, J. K. Hubler, G. K. 'Application of a High-Resolution Magnetic Spectrometer to Near-Surface Analysis' <i>Meyer, G. Linker and F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 457-69 (1976)</i> <i>Comment : R, dR. 2-60 keV 209Bi, 60 keV 69Ga -> Si</i>	1976-Hirv
1976	Sood, D. K. Dearnaley, G. 'Ion-Implanted Surface Alloys in Copper and Aluminum' <i>G. Carter, J. S. Colligon, W. A. Grant (Ed.): Appl. of Ion Beams to Materials. Inst. of Physics Conf. Ser. No. 28, 169-203 (1976)</i> <i>Comment : R. (150-300) keV Au, Mo, Bi, Ta, Mo, Gd, Bi, Cu, Rb, Ru, Cs, Ce, Eu, Ag, Cu, Se, Au -> Cu; Rb, Cd, Cs -> Al.</i>	1976-Sood
1979	Santry, D. C. Werner, R. D. Westcott, O. M. 'The Range of 120 keV Ions in Solids' <i>IEEE Trans. Nucl. Sci., Ns-26, 1331-1334 (1979)</i> <i>Comment : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -> Be, C, Al, Si</i>	1979-Sant
1980	Besenbacher, F. Bottiger, J. Laursen, T. Loftager, P. Moller, W. 'Z1-Oscillations in Low-Energy Heavy-Ion Ranges' <i>Nucl. Inst. Methods, 170, 183-188 (1980)</i> <i>Comment : R, dR. Atomic Numbers 18-92 (epsilon=.015) -> Si</i>	1980-Bese2
1980	Kalbitzer, S. Oetzmann, H. 'Ranges and Range Theories' <i>Rad. Effects, 47, 57-72, (1980)</i> <i>Comment : R, dR. .1-2 MeV Bi, Sb, As, Ge, P, Au, Cs, Eu, Gd Tb -> Si, Ge, C, Al</i>	1980-Kalb
1982	Geissel, H. Laichter, Yl Schneider, W. F. W. Armbruster, P. 'Energy Loss and Energy Loss Straggling of Fast Heavy Ions in Matter' <i>Nucl. Inst. Methods, 194, 21-29 (1982)</i> <i>Comment : S. Heavy Ions (18 - 92) at 0.5-10 MeV/amu -> 17 Solids and 5 Gases</i>	1982-Geis
1982	OConnor, D. J. 'Accurate RBS Determination of the Range Profile of Implanted Bismuth in Silicon' <i>Nucl. Inst. Methods, 196, 493-497 (1982)</i> <i>Comment : R. Bi (26-120 keV) -> Si</i>	1982-OCon
1985	Behar, M. Fichtner, P. F. Olivieri, C. A. DeSouza, J. P. Zawislak, F. C. 'Range Profiles of Implanted Bi and Au in Amorphous Silicon' <i>Nucl. Inst. Methods, B6, 453-458 (1985)</i> <i>Comment : R, dR. Bi, Au (10-390 keV) -> Si</i>	1985-Beha
1985	Fink, D. Biersack, J. P. Chen, J. T. Stadele, M. Tjan, K. 'Distributions of Light Ions and Foil Destruction after Irradiation of Organic Polymers' <i>J. Appl. Phys., 58, 668-676 (1985)</i> <i>Comment : R. H, He, Li, B, C, N, Bi (50-300 keV) -> AZ111, PMMA, Epoxy, C, Li, PMCN</i>	1985-Fink

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1985	Geissel, H. Lennard, W. N. Andrews, H. R. Jackson, D. P. Mitchell, I. V. 'Energy-Angle Distribution Measurements for 0.8 Vo Ne and Bi Ions Penetrating Thin Carbon Foils' <i>Nucl. Inst. Methods, B12, 38 (1985)</i> <i>Comment : Ne, Bi (20 keV/amu) -> C (angular effects)</i>	1985-Geis
1986	Lennard, W. N. Geissel, H. Jackson, D. P. Phillips, D. 'Electronic Stopping Values for Low Velocity Ions ($9 \leq Z1 \leq 92$) in Carbon Targets' <i>Nucl. Inst. Methods, B13, 127 (1986)</i> <i>Comment : S. (16 keV/amu) F, Ne, Na, Mg, Al, P, Cl, Ar, K, Sc, Cr, Mn, Cu, Kr, Nb, Ag, In, Xe, Sm, Yb, Au, Bi, U -> C</i>	1986-Lenn2
1987	Grande, P. L. Fichtner, P. F. P. Behar, M. Livi, R. P. Zawislak, F. C. 'Projected Ranges and Range Straggling of Au and Bi Implanted into Carbon' <i>Nucl. Inst. Methods, B19/20, 25-27 (1987)</i> <i>Comment : R, dR. Au, Bi (10-400 keV) -> C, SiO2</i>	1987-Gran
1988	Guimaraes, R. B. Amaral, L. Behar, M. Zawislak, F. C. Fink, D. 'Range Measurements and Thermal Stability Study of AX-111 Photoresist Implanted with Bi Ions' <i>J. Appl. Phys., 63, 2502-2506 (1988)</i> <i>Comment : R, dR. Bi (10-400 keV) -> AZ1111 photoresist</i>	1988-Guim
1988	Wilson, R. G. '(111) Random and (110) Channeling Implantation Profiles and Range Parameters in HgCdTe' <i>J. Appl. Phys., 63, 5302-5311 (1988)</i> <i>Comment : R, dR. 45 Ions (H to Ta) at 100-700 keV -> HgCdTe</i>	1988-Wils
1988	Wilson, R. G. 'Ion Implantation and SIMS Profiling of Impurities in II-VI Materials HgCdTe and CdTe' <i>J. Crystal Growth, 86, 735-743 (1988)</i> <i>Comment : R, dR. 52 Ions (H-Hg) at 100-700 keV -> CdTe, HgCdTe</i>	1988-Wils2
1993	Dwivedi, K. K. Kocsis, Z. Varer, P. Brand, R. 'Mean Ranges of Bi-209 Ions in ZnP Glass Detector' <i>Nucl. Tracks Rad. Meas. (UK), 22, 47-49 (1993)</i> <i>Comment : S,R. Bi -> ZnP</i>	1993-Dwiv
2000	Weick, H. Geissel, H. Scheidenberger, C. Attallah, F. Cortina, D. 'Drastic Enhancement of Energy-Loss Straggling of Relativistic Heavy Ions due to Charge-State Fluctuations' <i>Phys. Rev. Lett., 85, 2725-2728 (2000)</i> <i>Comment : dS. Au, Pb, Bi (100 - 1000 MeV/u) -> Be,Ag,Au,Ta,Pb,Al,Bi,Cu,</i>	2000-Weic

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2000	Weick, H. Geissel, H. Scheidenberger, C. Attallah, F. Baumann, T. 'Slowing Down of Relativistic Few-Electron Heavy Ions' <i>Nucl. Inst. Methods, B164-165, 168-179 (2000)</i> <i>Comment : S. Au, Pb, Bi (100 - 1000 MeV/u) -> Be,Al,Cu,Ag,Ta,Au,Pb</i>	2000-Weic2
